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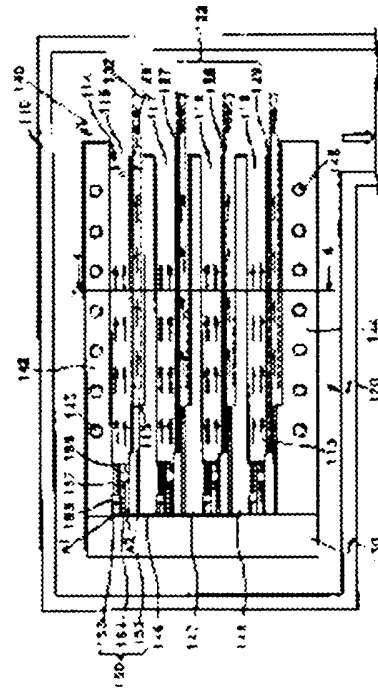
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(54) ATOMIC LAYER VAPOR DEPOSITION DEVICE CAPABLE OF VAPOR- DEPOSITING THIN FILM ON PLURAL SUBSTRATE

(57)Abstract:

PROBLEM TO BE SOLVED: To provide an atomic layer vapor deposition device capable of vapor- depositing thin films on plural substrates.

SOLUTION: This vapor deposition device is provided with a vacuum chamber 110 and a reactor 120 provided at the inside of the vacuum chamber. The reactor is provided with separable plural modules 140 and a gas feeding part 130. By assembling the modules, an opening A and plural stages 114 for storing substrates are formed. Reaction gas and purge gas are fed from the gas feeding part 130 into the reactor. Gas feeding lines 150 for pouring each gas into the stage parts are formed at the modules. By this vapor deposition device, thin films having good properties can be vapor-deposited on plural substrates having fine patterns at one time.



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